

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
85V	1.7mΩ@10V	310A

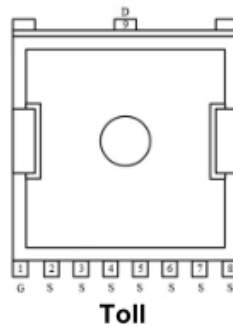
## Feature

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

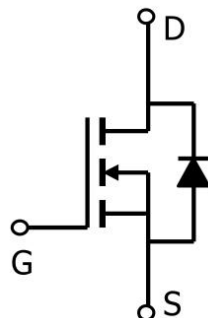
## Applications

- Power switching application
- DC-DC Converter
- Uninterruptible power supply

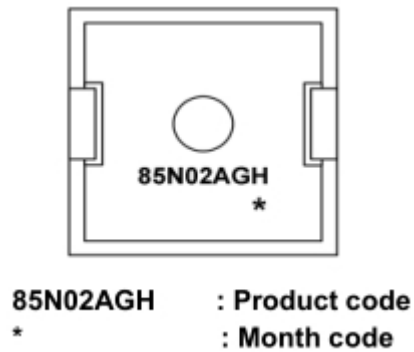
## Package



## Circuit diagram



## Marking



## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain source voltage	V <sub>DS</sub>	85	V
Gate source voltage	V <sub>GS</sub>	±20	V
Continuous drain current(Tc=25°C)	I <sub>D</sub>	310	A
Pulsed drain current	I <sub>DM</sub>	1240	A
Power dissipation(Tc=25°C)	P <sub>D</sub>	420	W
Single pulsed avalanche energy <sup>1)</sup>	E <sub>AS</sub>	405	mJ
Thermal resistance, junction-case	R <sub>θJC</sub>	0.35	°C/W
Operation and storage temperature	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

## Electrical characteristics

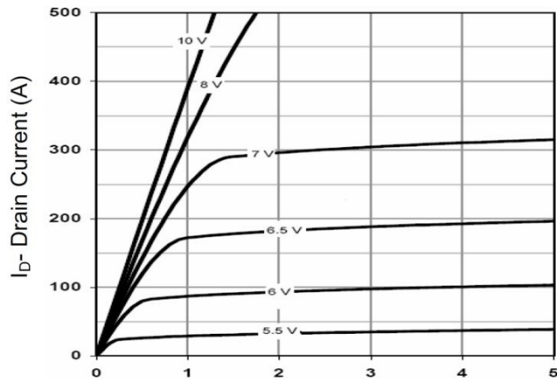
(T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	80			V
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> =68V, V <sub>GS</sub> = 0V			1	uA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±0.1	uA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	2.8	4.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		1.7	2.5	mΩ
Dynamic Characteristics						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, f=1MHz		9860		pF
Output capacitance	C <sub>oss</sub>			1670		
Reverse transfer capacitance	C <sub>rss</sub>			76		
Switching Characteristics						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =10V, I <sub>D</sub> =165A		143		pF
Gate-Source Charge	Q <sub>gs</sub>			51		
Gate-Drain Charge	Q <sub>gd</sub>			25		
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =40V, I <sub>D</sub> =165A, R <sub>G</sub> =1.6Ω		27		nS
Turn-on Rise Time	T <sub>r</sub>			75		
Turn-Off Delay Time	T <sub>d(off)</sub>			86		
Turn-Off Fall Time	t <sub>f</sub>			35		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V			1.2	V

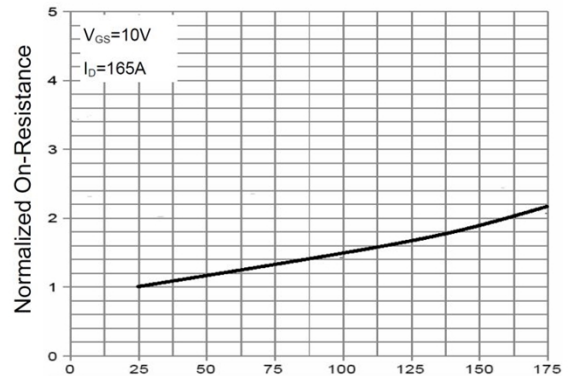
### Note:

1. E AS is tested at starting T<sub>j</sub> = 25°C, V<sub>DD</sub> = 45V, V<sub>GS</sub> = 10V, L = 0.1mH, R<sub>G</sub> = 25Ω;

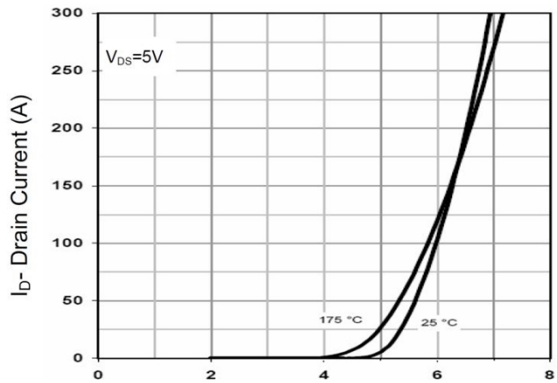
## Typical Characteristics



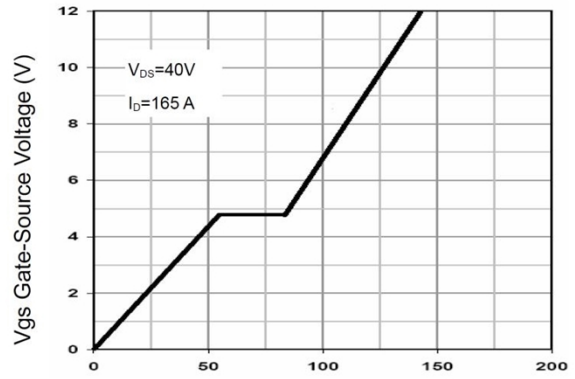
$V_{ds}$ -Drain-Source Voltage (V)  
Output Characteristics



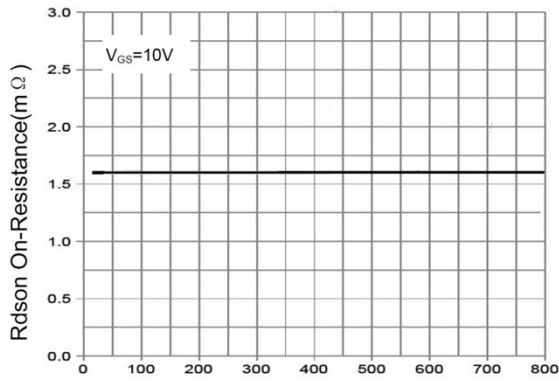
$T_J$ -Junction Temperature ( $^{\circ}\text{C}$ )  
 $R_{ds(on)}$ -Junction Temperature



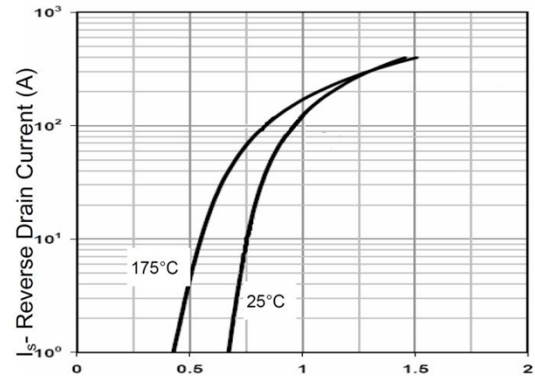
$V_{gs}$ -Gate-Source Voltage (V)  
Transfer Characteristics



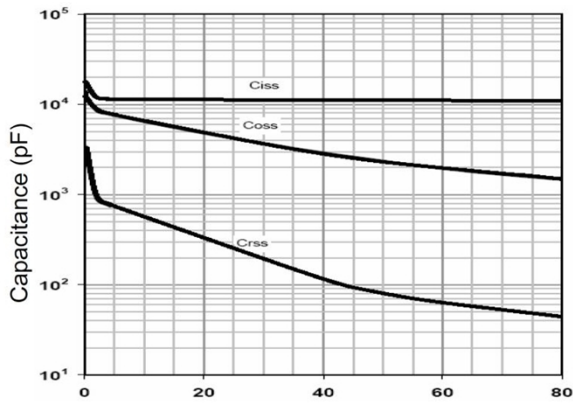
$Q_g$ -Gate Charge (nC)  
Gate Charge



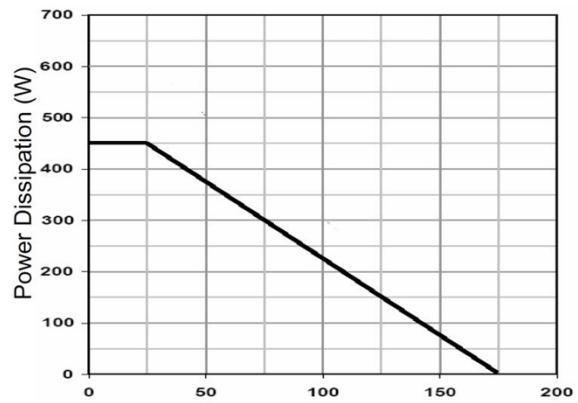
$I_D$ -Drain Current (A)  
 $R_{ds(on)}$ -Drain Current



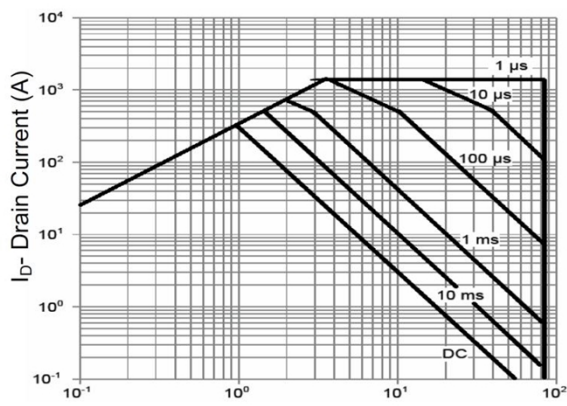
$V_{sd}$ -Source-Drain Voltage (V)  
Source-Drain Diode Forward



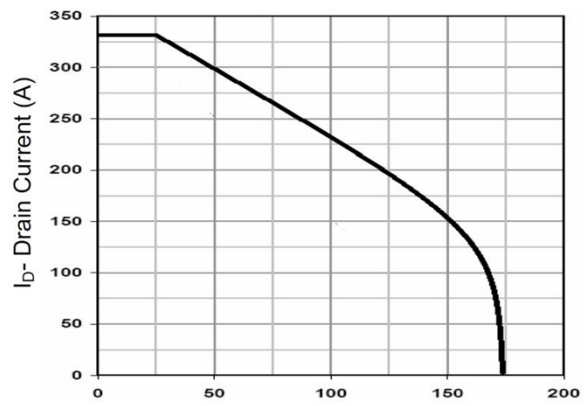
Vds Drain-Source Voltage (V)  
Capacitance vs Vds



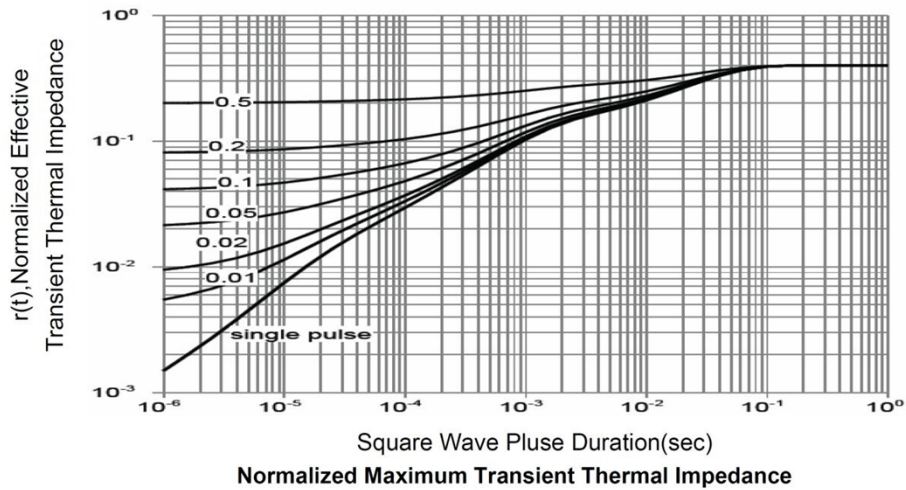
Tj-Junction Temperature (°C)  
Power De-rating



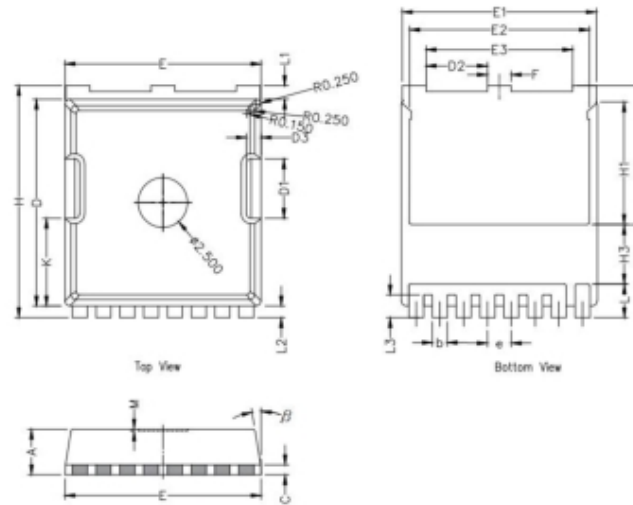
Vds Drain-Source Voltage (V)  
Safe Operation Area



Tj-Junction Temperature (°C)  
Current De-rating



# TOLL Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.7	0.85
L2	0.45	0.6	0.75
M	0.08 REF.		
$\beta$	8°	10°	12°
K	4.25	4.40	4.55